

IN THE SPECIFICATION

After the section title "CROSS REFERENCE", but before the section title "FIELD OF THE INVENTION", please insert the following paragraphs: ✓

--The subject matter of the present reissue application is related to co-pending reissue application entitled "Inspecting Optical Masks With Electron Beam Microscopy," said application having Serial No. 09/502,534, which reissue application was also filed on February 10, 2000. The present reissue application, Serial No. 09/502,120, and the co-pending reissue application, Serial No. 09/502,534, are each a reissue of U.S. Application No. 08/606,854 filed February 26, 1996, now U.S. Patent No. 5,717,204.--

Please delete the paragraph at col. 11, lines 19-37 and replace it with the following: ✓

The diameter of the scanning beam 100 and its current are determined by several factors. The angular emission from the source ($1.0 \text{ [Ma]mA/steradians}$), and the aperture angle defined by final aperture 99 determine the beam current. The probe diameter is determined by aberrations in both lenses, which are designed for high excitation (field width/focal length) to minimize both spherical and chromatic aberration. The effect of beam interactions (i.e. statistical blurring due to repulsion between individual beam electrons) are also important in this high current system, accounting for about half the probe size on substrate 57. These effects are minimized by avoiding intermediate crossovers, by using a short beam path (40 cm.) and by using lenses with relatively large half angles at the source and substrate 57. To obtain a given spot size, the aperture diameter is chosen to balance all these effects while providing maximum possible current. In this system spot size is primarily adjusted using the aperture, although it is possible to change lens strengths to magnify or demagnify the beam from the source.